Salvatore Lombardo

List of Publications by Year
in descending order

16	1,126	933447 10	1058476 14
papers	citations	h-index	g-index

17	17	17	1286
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	A Review on Dielectric Breakdown in Thin Dielectrics: Silicon Dioxide, Highâ€k, and Layered Dielectrics. Advanced Functional Materials, 2020, 30, 1900657.	14.9	119
2	Imaging System Based on Silicon Photomultipliers and Light Emitting Diodes for Functional Near-Infrared Spectroscopy. Applied Sciences (Switzerland), 2020, 10, 1068.	2.5	8
3	Characterization of SiPMs With NIR Long-Pass Interferential and Plastic Filters. IEEE Photonics Journal, 2018, 10, 1-12.	2.0	25
4	Crucial aspects for the use of silicon photomultiplier devices in continuous wave functional near-infrared spectroscopy. Biomedical Optics Express, 2018, 9, 4679.	2.9	7
5	Characterization of a fiber-less, multichannel optical probe for continuous wave functional near-infrared spectroscopy based on silicon photomultipliers detectors: in-vivo assessment of primary sensorimotor response. Neurophotonics, 2017, 4, 1.	3.3	20
6	Improvement of sensitivity in continuous wave near infrared spectroscopy systems by using silicon photomultipliers. Biomedical Optics Express, 2016, 7, 1183.	2.9	28
7	Influence of gate oxides with high thermal conductivity on the failure distribution of InGaAs-based MOS stacks. Microelectronics Reliability, 2016, 56, 22-28.	1.7	6
8	Physical mechanism of progressive breakdown in gate oxides. Journal of Applied Physics, 2014, 115, .	2.5	34
9	Dark Current in Silicon Photomultiplier Pixels: Data and Model. IEEE Transactions on Electron Devices, 2012, 59, 2410-2416.	3.0	46
10	Electron Transport and Dielectric Breakdown Kinetics in Pr₂O₃High K Films. Advances in Science and Technology, 2006, 46, 21.	0.2	0
11	Breakdown kinetics of Pr2O3 films by conductive-atomic force microscopy. Applied Physics Letters, 2005, 87, 231913.	3.3	32
12	Dielectric breakdown mechanisms in gate oxides. Journal of Applied Physics, 2005, 98, 121301.	2.5	370
13	Percolation path and dielectric-breakdown-induced-epitaxy evolution during ultrathin gate dielectric breakdown transient. Applied Physics Letters, 2003, 83, 2223-2225.	3.3	90
14	Spatial separation mechanism in Si quantum dots deposited by chemical vapour deposition on SiO2. Materials Research Society Symposia Proceedings, 2003, 788, 1221.	0.1	0
15	Crystal grain nucleation in amorphous silicon. Journal of Applied Physics, 1998, 84, 5383-5414.	2.5	331
16	Mechanism and kinetics of the ion-assisted nucleation in amorphous silicon. Physical Review B, 1996, 53, 7742-7749.	3.2	10